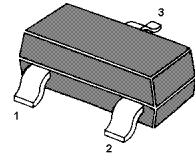


MMBT A94

PNP Silicon Epitaxial Planar Transistor

for high voltage switching and amplifier applications.

The transistor is subdivided into one group according to its DC current gain.



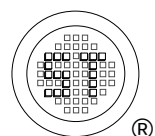
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

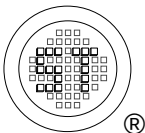
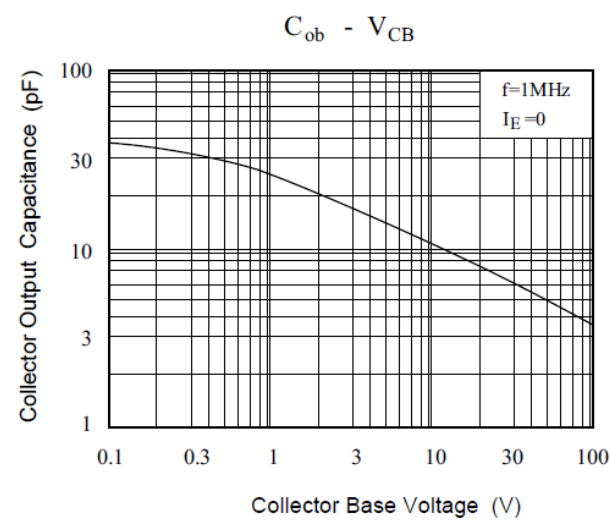
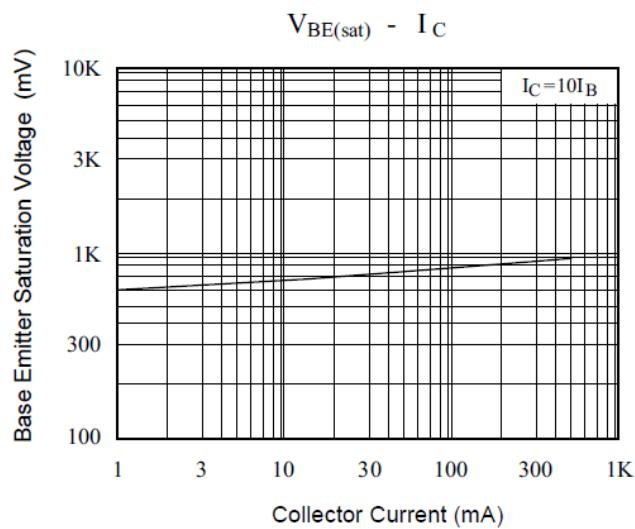
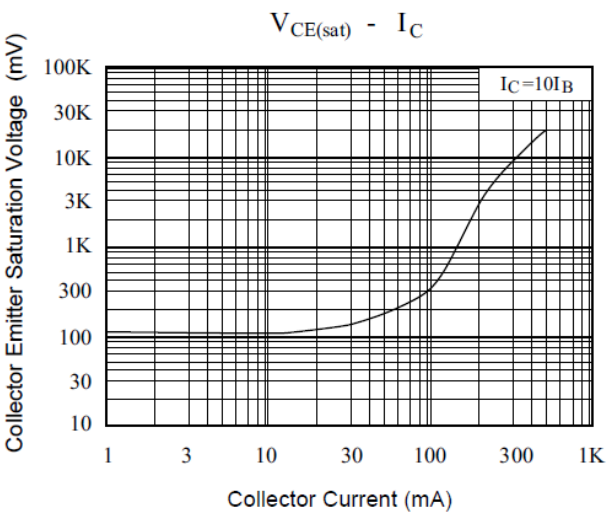
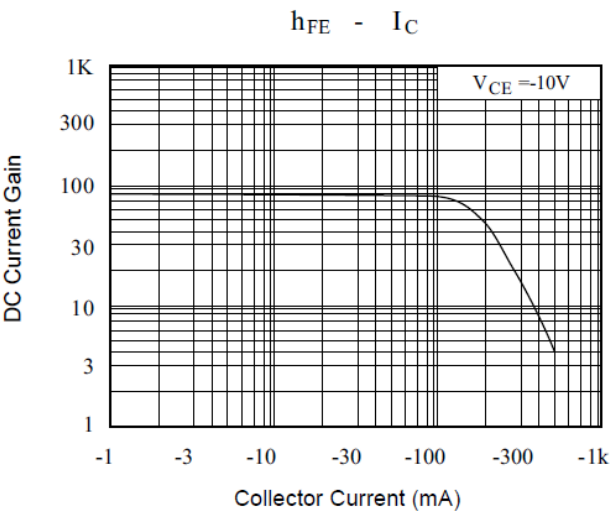
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	400	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	400	V
Emitter Base Voltage	$-V_{\text{EBO}}$	6	V
Collector Current	$-I_{\text{C}}$	300	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{\text{CE}} = 10 \text{ V}$, $-I_{\text{C}} = 1 \text{ mA}$ at $-V_{\text{CE}} = 10 \text{ V}$, $-I_{\text{C}} = 10 \text{ mA}$ at $-V_{\text{CE}} = 10 \text{ V}$, $-I_{\text{C}} = 30 \text{ mA}$	h_{FE} h_{FE} h_{FE}	100 40 25	- - -	- - -
Collector Base Cutoff Current at $-V_{\text{CB}} = 300 \text{ V}$	$-I_{\text{CBO}}$	-	0.1	μA
Collector Emitter Cutoff Current at $-V_{\text{CE}} = 400 \text{ V}$	$-I_{\text{CES}}$	-	1	μA
Emitter Base Cutoff Current at $-V_{\text{EB}} = 4 \text{ V}$	$-I_{\text{EBO}}$	-	0.1	μA
Collector Base Breakdown Voltage at $-I_{\text{C}} = 100 \mu\text{A}$	$-V_{(\text{BR})\text{CBO}}$	400	-	V
Collector Emitter Breakdown Voltage at $-I_{\text{C}} = 1 \text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	400	-	V
Collector Emitter Breakdown Voltage at $-I_{\text{C}} = 100 \mu\text{A}$	$-V_{(\text{BR})\text{CES}}$	400	-	V
Emitter Base Breakdown Voltage at $-I_{\text{E}} = 10 \mu\text{A}$	$-V_{(\text{BR})\text{EBO}}$	6	-	V
Collector Emitter Saturation Voltage at $-I_{\text{C}} = 10 \text{ mA}$, $-I_{\text{B}} = 1 \text{ mA}$ at $-I_{\text{C}} = 50 \text{ mA}$, $-I_{\text{B}} = 5 \text{ mA}$	$-V_{\text{CE(sat)}}$	- -	0.5 0.75	V
Base Emitter Saturation Voltage at $-I_{\text{C}} = 10 \text{ mA}$, $-I_{\text{B}} = 1 \text{ mA}$	$-V_{\text{BE(sat)}}$	-	0.75	V
Collector Output Capacitance at $-V_{\text{CB}} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	7	pF



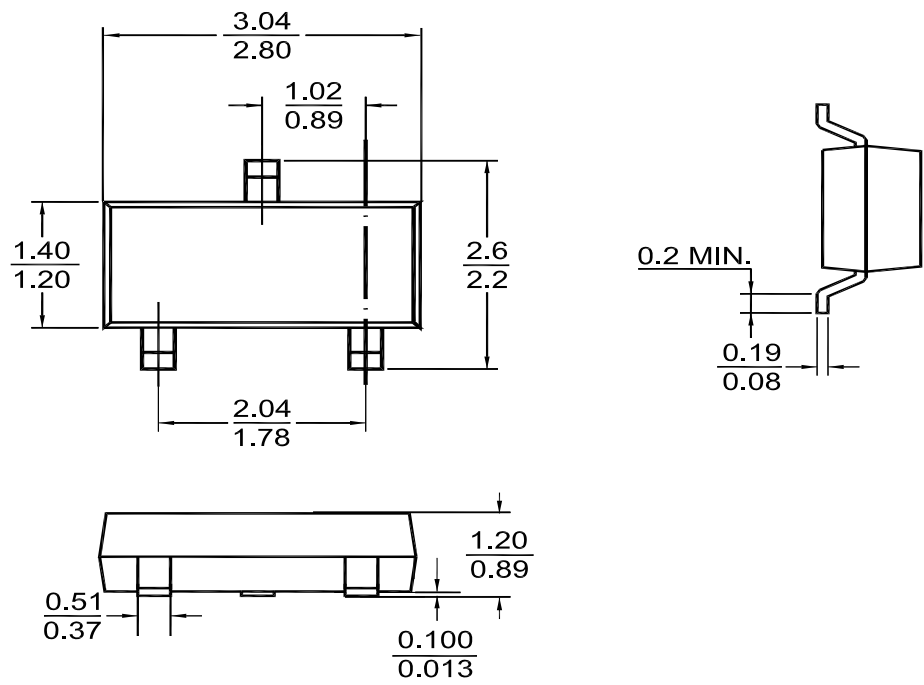


MMBTA94

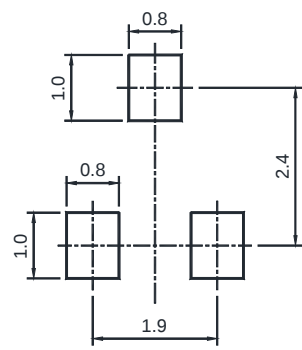
PACKAGE OUTLINE

Plastic surface mounted package (Dimensions in mm)

TO-236



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

